

Corrected
J1

ones of said active devices of said second substrate portion are intercoupled via metal lines.

31. (Amended) An apparatus comprising:

a primary substrate having a first level of devices formed thereon and defining a first device surface; and

J2

at least one secondary single crystal substrate having active devices formed thereon and defining a second device surface, wherein the first device surface of the primary substrate is connected directly to the second device surface of the at least one secondary single crystal substrate such that selected ones of said active devices of said at least one secondary single crystal substrate are intercoupled via metal lines to selected ones of the first level of devices of the primary substrate.

[Please add the following new claim:]

J3

--37. (New) The apparatus of claim 28, wherein the first substrate portion is formed as a film of less than an entire portion of a starting material by demarcating a film thickness through an ion implantation into the starting material and separating the first substrate portion from the starting material.--